



60V 175°C PNP LOW SAT MEDIUM POWER TRANSISTOR IN POWERDI5060-8

Features

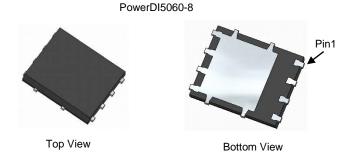
- BV_{CEO} > -60V
- I_C = -3A Continuous Collector Current
- I_{CM} = -8A Peak Pulse Current
- R_{CE(SAT)} < 120 mΩ
- Rated to +175°C—Ideal for High Ambient Temperature Environments
- Complementary Part DXTN3C60PS
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

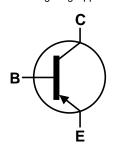
Mechanical Data

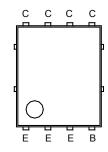
- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish—Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 [®]
- Weight: 0.097 grams (Approximate)

Applications

- Power Management
- Load Switch
- Linear Mode Voltage Regulator
- Backlighting Applications







Internal Schematic

Top View Pin Configuration

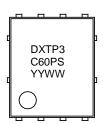
Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXTP3C60PS-13	AEC-Q101	DXTP3C60PS	13	12	1000

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, see http://www.diodes.com/products/packages.html.

Marking Information



DXTP3 = Product Type Marking Code C60PS = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-7	V
Base Current	I _B	-1	Α
Continuous Collector Current	Ic	-3	Α
Peak Pulse Collector Current	I _{CM}	-8	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)	PD	5	W	
Thermal Resistance, Junction to Lead	(Note 5)	R _{ÐJL}	5.6	°C/W	
Thermal Decistores, Junction to Ambient	(Note 5)	D	73	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{OJA}	30		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C	

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

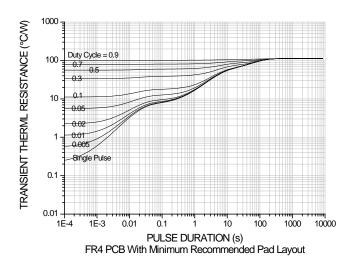
Notes:

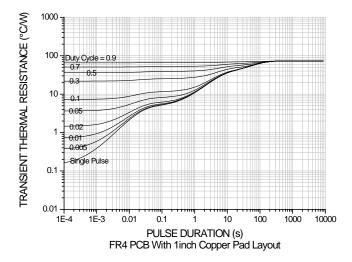
^{5.} For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

^{6.} Same as Note 5, except the device is measured at $t \le 5$ sec. 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information







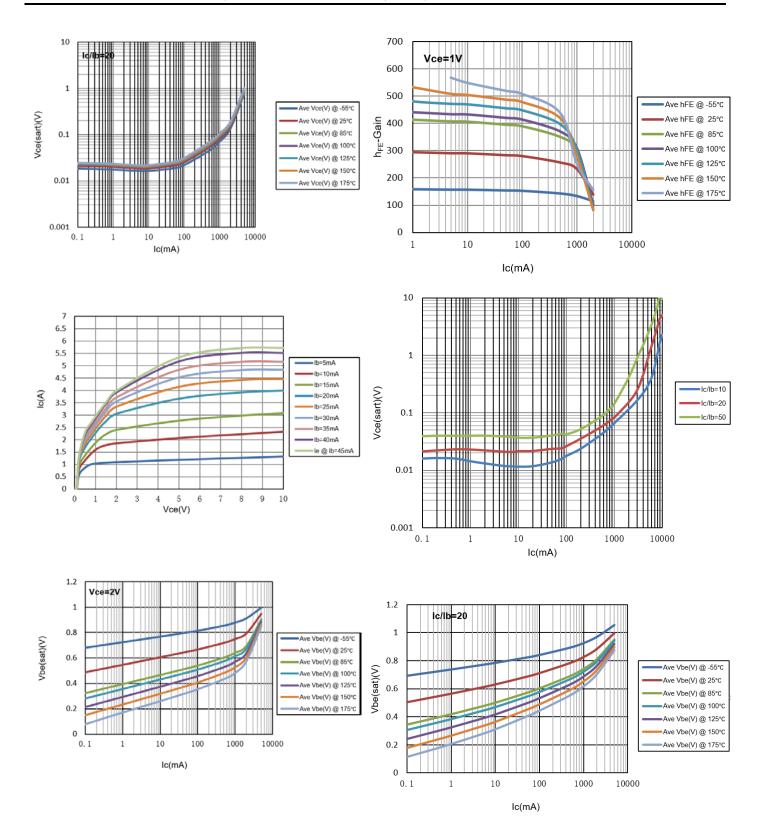
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	BV _{CBO}	-60	_	_	V	$I_{C} = -100\mu A$	
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	-60	_	_	V	$I_C = -10mA$	
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	I _E = -100μA	
Collector-Base Cutoff Current	I _{CBO}	_	_	-100	nA	V _{CB} = -48V	
Collector-base Cuton Current		_	_	-50	μΑ	V _{CB} = -48V @ Tj = 150°C	
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	V _{EB} = -7V	
Collector-Emitter Cutoff Current	I _{CES}	_	_	100	nA	V _{CES} = -48V	
ON CHARACTERISTICS (Note 9)							
		150	250	_		$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$	
DC Current Gain	h	150	225	_		$I_C = -1A$, $V_{CE} = -2V$	
De current Gain	h _{FE}	80	130		_	I _C = -2A, V _{CE} = -2V	
		35	75			I _C = -3A, V _{CE} = -2V	
Calleston Fraitten Catamatica Valtana	.,	_	-100	-225	mV	I _C = -1A, I _B = -50mA	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	-240	-360		I _C = -3A, I _B = -300mA	
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_	100	225	mΩ	I _C = -1A, I _B = -50mA	
Collector-Emilier Saturation Resistance		_	80	120		$I_C = -3A$, $I_B = -300mA$	
Base-Emitter Saturation Voltage	.,	_	-0.8	-0.95	V	$I_C = -1A$, $I_B = -50mA$	
Base-Efficier Saturation Voltage	V _{BE(sat)}	_	-1.02	-1.2		$I_C = -2A$, $I_B = -200mA$	
Base-Emitter Turn-On Voltage	V _{BE(on)}	_	-0.7	-0.8	V	I _C = -0.5A, V _{CE} = -2V	
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product	f⊤	_		_	MHz	$V_{CE} = -10V$, $I_{C} = -500$ mA, $f = 100$ MHz	
Output Capacitance	C _{obo}	_	42	_	pF	V _{CB} = -10V, f = -1MHz	
Delay Time	t _d	_	15		ns		
Rise Time	t _r	_	220	_	ns]	
Turn-On Time	t _(on)	_	235	_	ns	V _{CC} = -12.5V, I _C = 3A	
Storage Time	ts		160	_	ns	$I_{B1} = -I_{B2} = -0.150A$	
Fall Time	t _f	_	185	_	ns		
Turn-Off Time	t _(off)	_	345	_	ns		

Note: 8. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

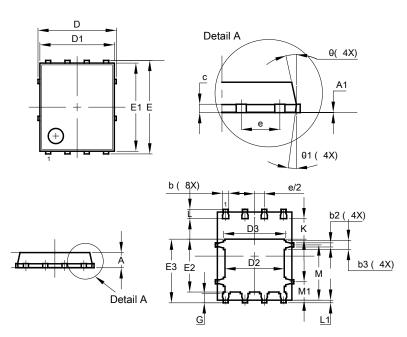




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

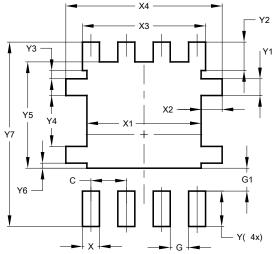


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	_		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	5.15 BSC				
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	_	_		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
M	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All	All Dimensions in mm				

Suggested Pad Layout

 $\label{please} Please see \ http://www.diodes.com/package-outlines.html for the latest version.$

PowerDI5060-8



Dimensions	Value (in mm)				
С	1.270				
G	0.660				
G1	0.820				
Х	0.610				
X1	4.100				
X2	0.755				
Х3	4.420				
X4	5.610				
Υ	1.270				
Y1	0.600				
Y2	1.020				
Y3	0.295				
Y4	1.825				
Y5	3.810				
Y6	0.180				
Y7	6.610				

July 2018



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